

General Description

The WSD86P10DN56 is the highest performance trench P-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSD86P10DN56 meet the RoHS and Green Product requirement,100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

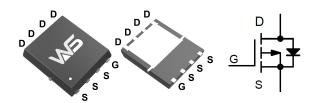
Product Summery

BVDSS	RDSON	ID
-100V	17mΩ	-86A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

DFN5X6_8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter Rating		Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25℃	Continuous Drain Current, -V _{GS} @ -10V ¹	-86	Α
I _D @T _C =100°C	Continuous Drain Current, -V _{GS} @ -10V ¹ -55		А
I _{DM}	Pulsed Drain Current ² -280		А
EAS	Single Pulse Avalanche Energy ³	729	mJ
I _{AS}	Avalanche Current	-54	А
P _D @T _C =25°C	Total Power Dissipation ⁴	Total Power Dissipation ⁴ 250	
T _{STG}	Storage Temperature Range -55 to 150		$^{\circ}$
TJ	Operating Junction Temperature Range	-55 to 150	$^{\circ}$

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-Ambient ¹		62	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹		0.5	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-100			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25℃, I _D =-1mA		-0.021		V/℃
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-20A		17	28	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.4	-2.1	-2.8	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	VGS-VDS, ID250UA		4.08		mV/℃
less	Drain-Source Leakage Current	V_{DS} =-80V , V_{GS} =0V , T_J =25 $^{\circ}$ C	s=-80V , V _{GS} =0V , T _J =25℃		1	— uA
I _{DSS}	Drain-Source Leakage Guiterit	V_{DS} =-80V , V_{GS} =0V , T_{J} =55 $^{\circ}$ C			5	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 20 V$, V_{DS} = $0 V$			±100	nA
gfs	Forward Transconductance	V _{DS} =-10V , I _D =-20A	30			S
Q_g	Total Gate Charge (-4.5V)	V _{DS} =-30V , V _{GS} =-10V , I _D =-20A		110		
Q_{gs}	Gate-Source Charge			15		nC
Q_gd	Gate-Drain Charge			18		
T _{d(on)}	Turn-On Delay Time			27		
Tr	Rise Time	V_{DD} =-30V , V_{GS} =-10V ,		15		ne
$T_{d(off)}$	Turn-Off Delay Time	R_G =6Ω, I_D =-10A ,RL=30Ω.		104		- ns
T _f	Fall Time			57		
C _{iss}	Input Capacitance	V _{DS} =-30V , V _{GS} =0V , f=1MHz		6105		
C _{oss}	Output Capacitance			728		pF
C _{rss}	Reverse Transfer Capacitance			258		

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =-30V , L=0.5mH , I _{AS} =-54A	300			mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current			-86	Α
V_{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-10A , T _J =25℃			-1.2	V

Note

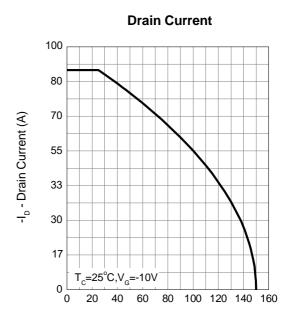
- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t≦10sec.
- 2.The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%
- 3. The EAS data shows Max. rating . The test condition is V_{DD} =-30V, V_{GS} =-10V, L=0.5mH, I_{AS} =-54A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Operating Characteristics

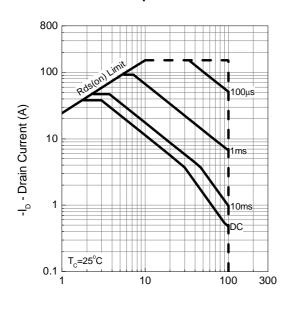
Power Dissipation 300 200 100 80 60 30 T_c=25°C 0 20 40 60 80 100 120 140 160

T_j - Junction Temperature (°C)



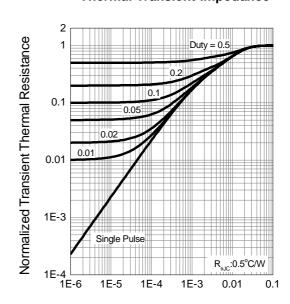
T_i - Junction Temperature (°C)

Safe Operation Area



-V_{DS} - Drain - Source Voltage (V)

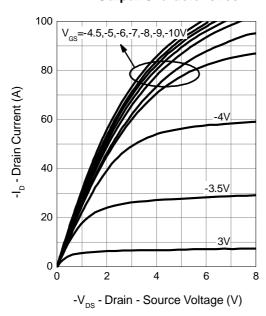
Thermal Transient Impedance



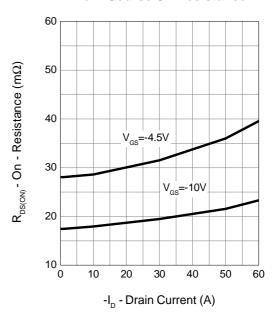
Square Wave Pulse Duration (sec)



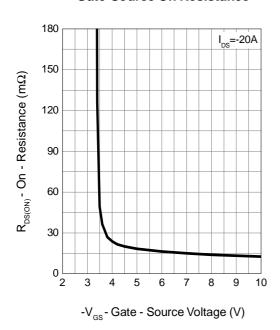
Output Characteristics



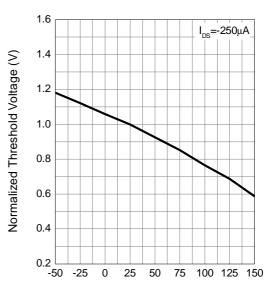
Drain-Source On Resistance



Gate-Source On Resistance



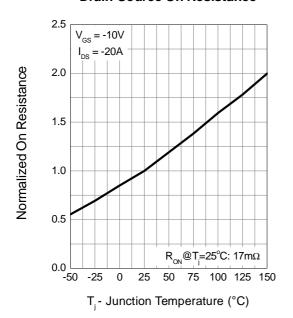
Gate Threshold Voltage



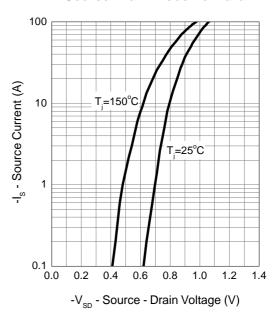
T_i - Junction Temperature (°C)



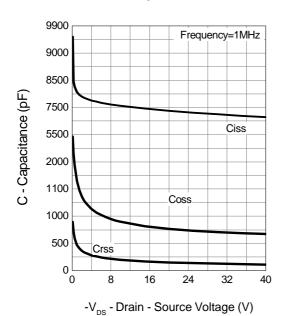
Drain-Source On Resistance



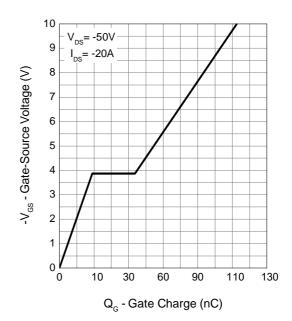
Source-Drain Diode Forward



Capacitance



Gate Charge





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